

CS20S40CT-A / CS20S45CT-A

20A Low Barrier Diode

■ Features

- · Low forward voltage drop.
- Excellent high temperature stability.
- Fast switching capability.
- Suffix "G" indicates Halogen-free part, ex.CS20S40CTG-A.
- Lead-free parts meet environmental standards of MIL-STD-19500 /228

■ Mechanical data

• Epoxy: UL94-V0 rated flame retardant.

• Case: JEDEC TO-220AB molded plastic body.

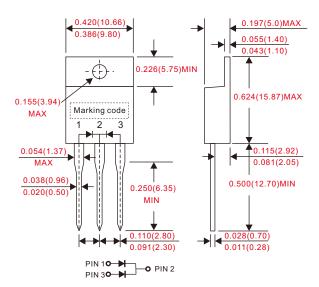
• Terminals : Solder plated, solderable per MIL-STD-750, Method 2026.

Polarity: As marked.Mounting Position : Any.

• Weight: Approximated 2.25 gram.

Outline

TO-220AB



Dimensions in inches and (millimeters)

■ Maximum ratings and electrical characteristics

Rating at 25° C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Parameter	Conditions	Symbol	CS20S40CT-A	CS20S45CT-A	─ UNIT
Marking code			CS20S40CT	CS20S45CT	
Peak repetitive reverse voltage		V _{RRM}			
Working peak reverse voltage		V_{RWM}	40	45	V
DC blocking voltage		V_{RM}			
Forward rectified current (total device)		Io	2	Α	
Forward surge current (per diode)	8.3ms single half sine-wave superimposed on rate load (JEDEC method)	I _{FSM}	28	А	
Peak repetitive reverse surge current (per diode)	2us - 1kHz	I _{RRM}	;	А	
Thermal resistance(1) (per diode)	Junction to case	R _{eJC}	2	°C/W	
Operating and Storage temperature		T _J , T _{STG}	-65 ~ +150		°C

Parameter	Conditions	Symbol	MIN.	TYP.	MAX.	UNIT
Forward voltage drop (per diode)	$I_F = 10A, T_J = 25^{\circ}C$	V _F			470	mV
	I _F = 10A, T _J = 125°C				440	
	$I_F = 20A, T_J = 25^{\circ}C$				600	
I Reverse current (per diode)	$V_R = V_{RRM} T_J = 25^{\circ}C$	- I _R			0.5	mA
	$V_R = V_{RRM} T_J = 125^{\circ}C$				100	

Note: 1.Thermal resistance from junction to case per leg, with heatsink size(1.35" x 0.95" x 0.18") Al-plate.

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■ Rating and characteristic curves

Fig.1 - Forward Current Derating Curve (per diode)

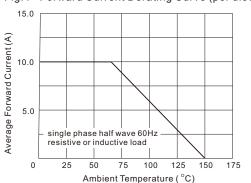


Fig. 2 - Instantaneous Forward Characteristics (per diode) 100 Instantaneous Forward Current (A) 10 T₄=125°C 1 T_A=100°C 0.1 T₄=25°C 0.01

0.2

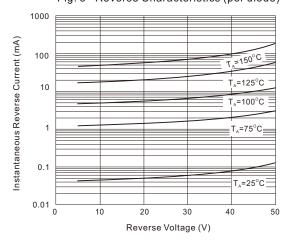
Instantaneous Forward Voltage (Volts)

0.3

0.4

0.5

Fig. 3 - Reverse Characteristics (per diode)



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